

Filmetrics F54

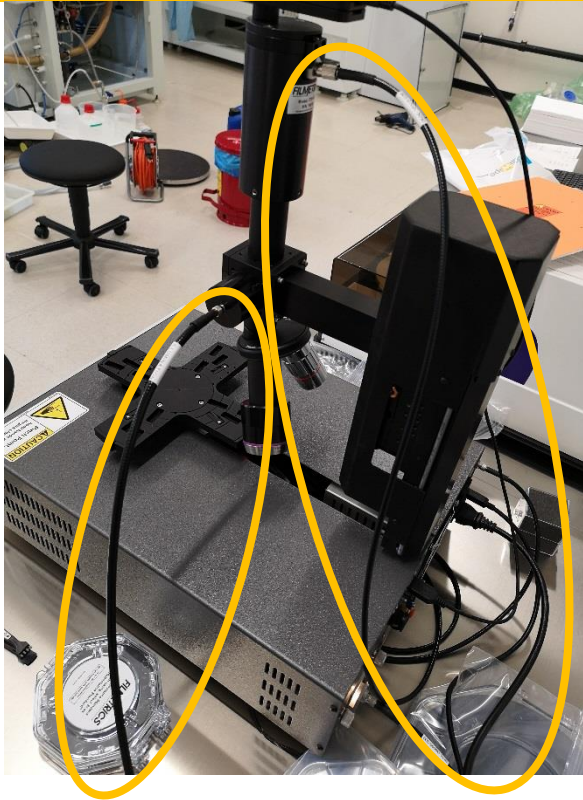
Thin Film Mapping Analyzer

User Manual

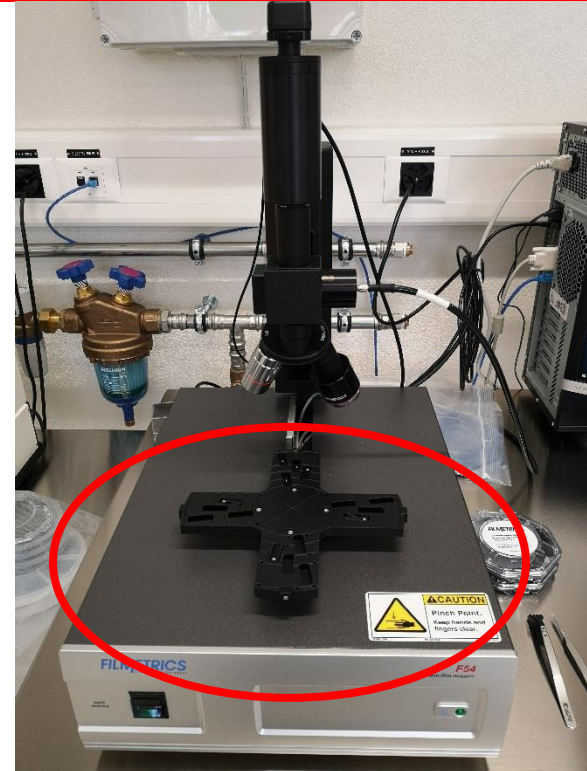


WARNINGS

DO NOT TOUCH/BEND THE FIBERS

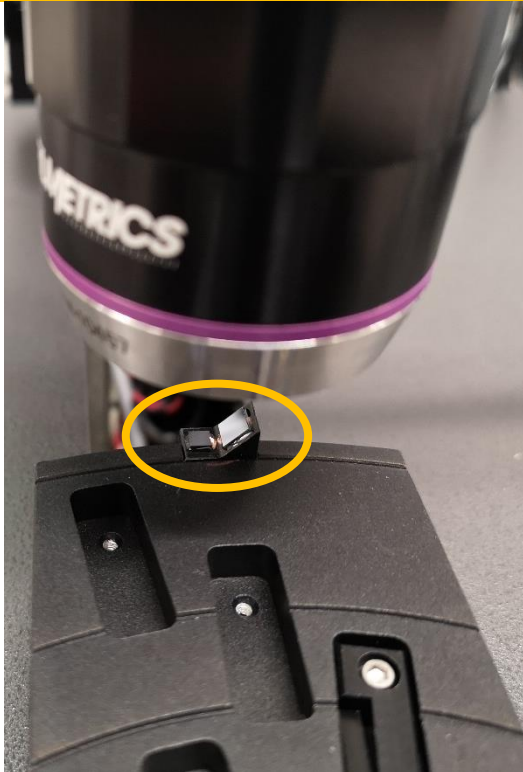


KEEP HANDS AWAY (high speed stage)

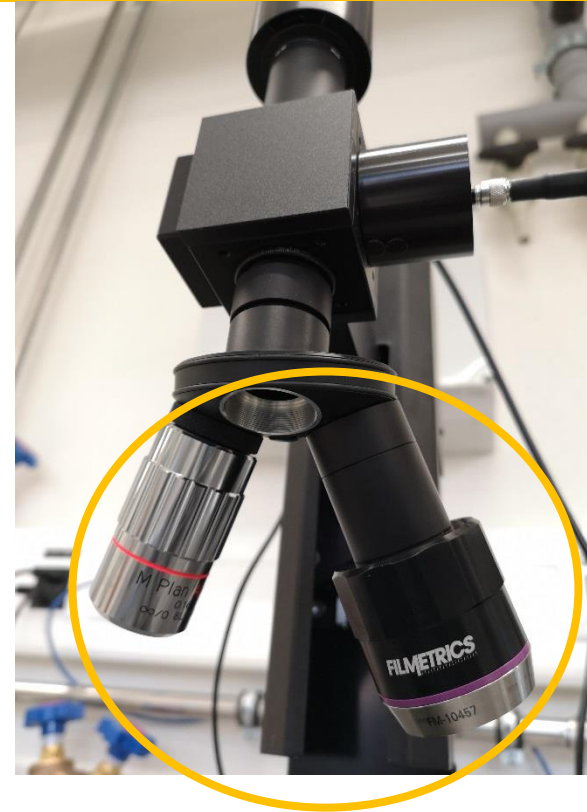


WARNINGS

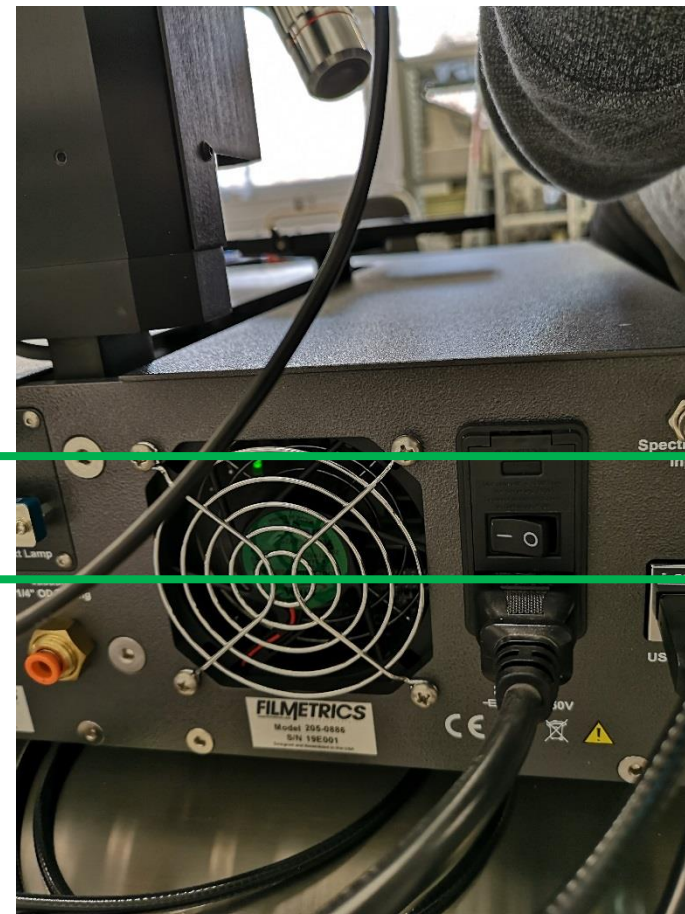
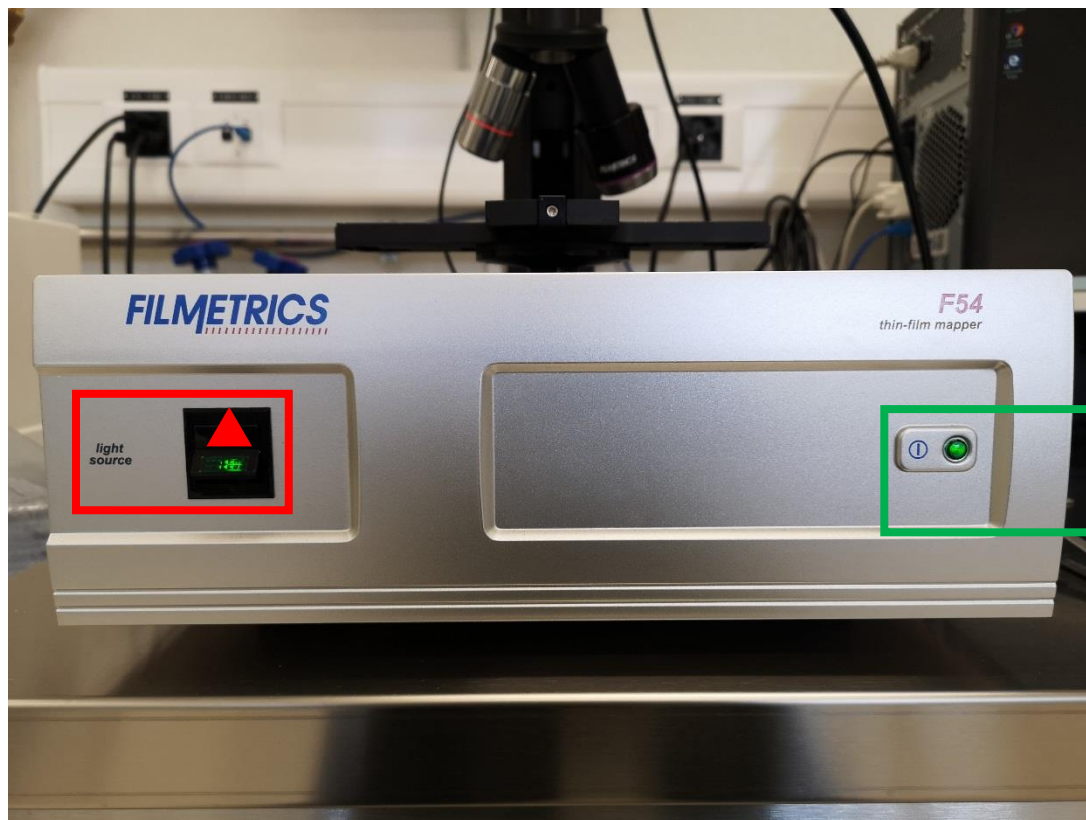
DO NOT TOUCH/SCRATCH:
stage reference & background mirror



AVOID SAMPLE CRASH:
Measurement objectives

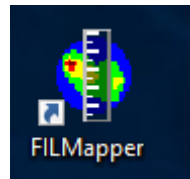


Turn the light source on



Tool usually
always ON

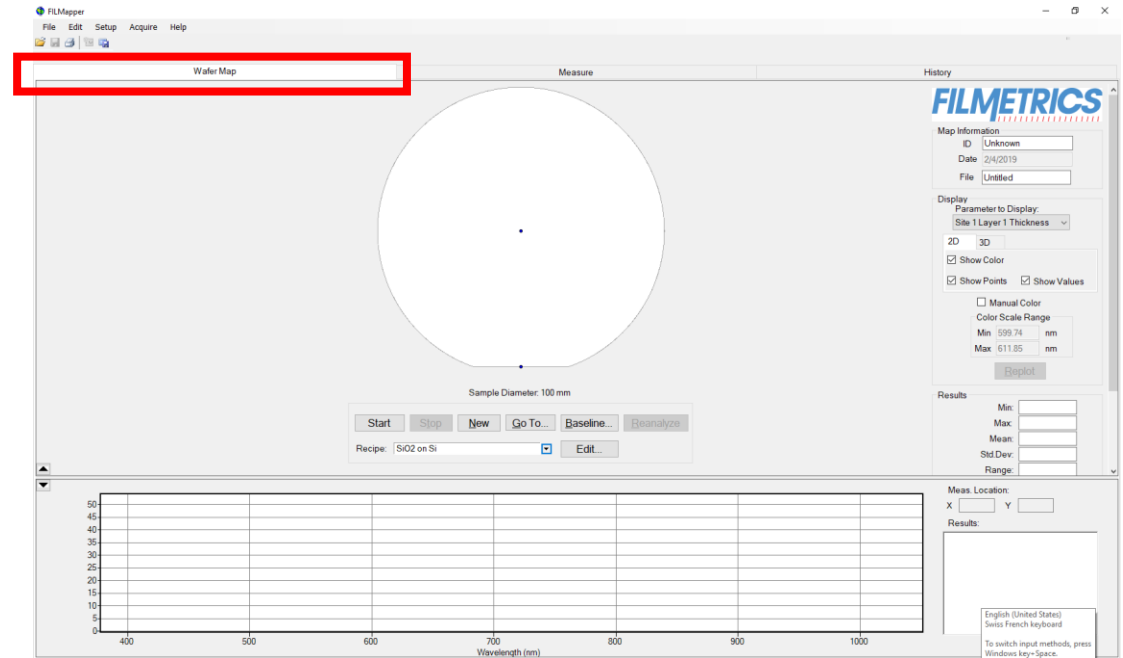
Start the FILMapper software



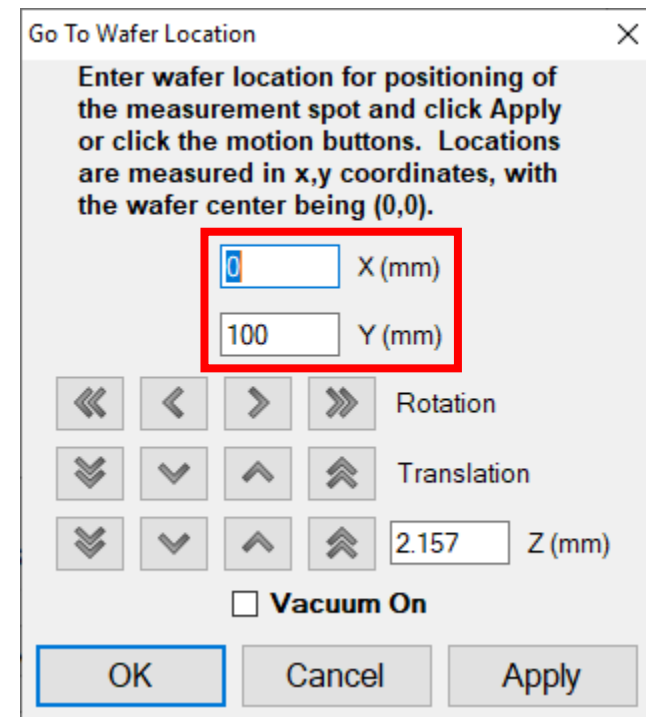
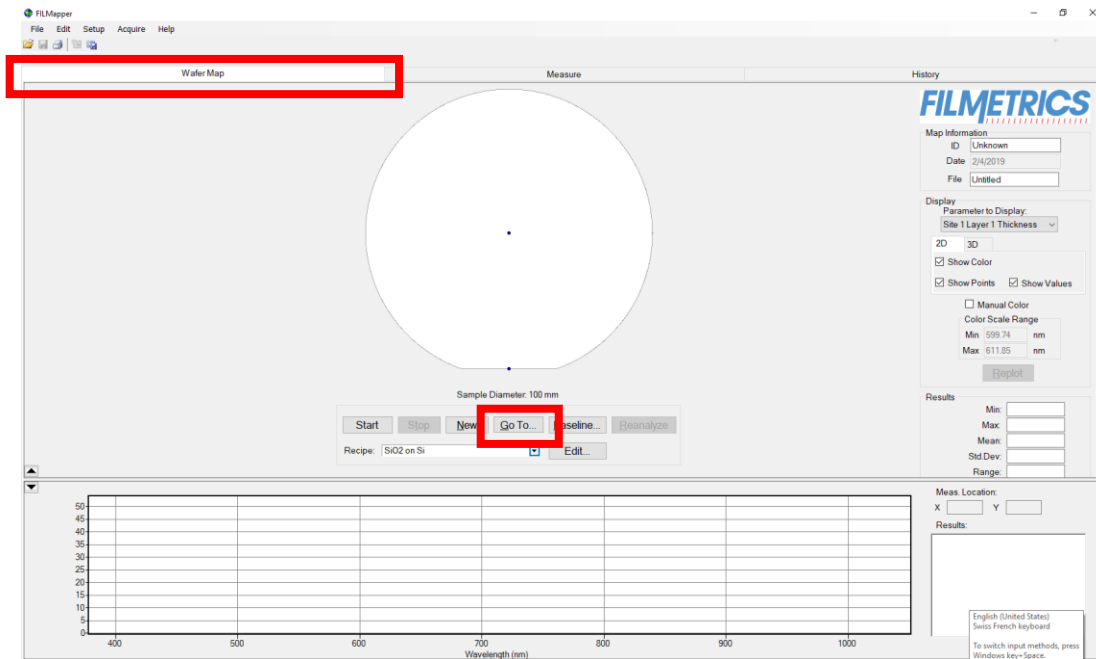
Please Wait ...

Searching for chuck motion limits...

Stage initializes without warnings:
KEEP HANDS AWAY!



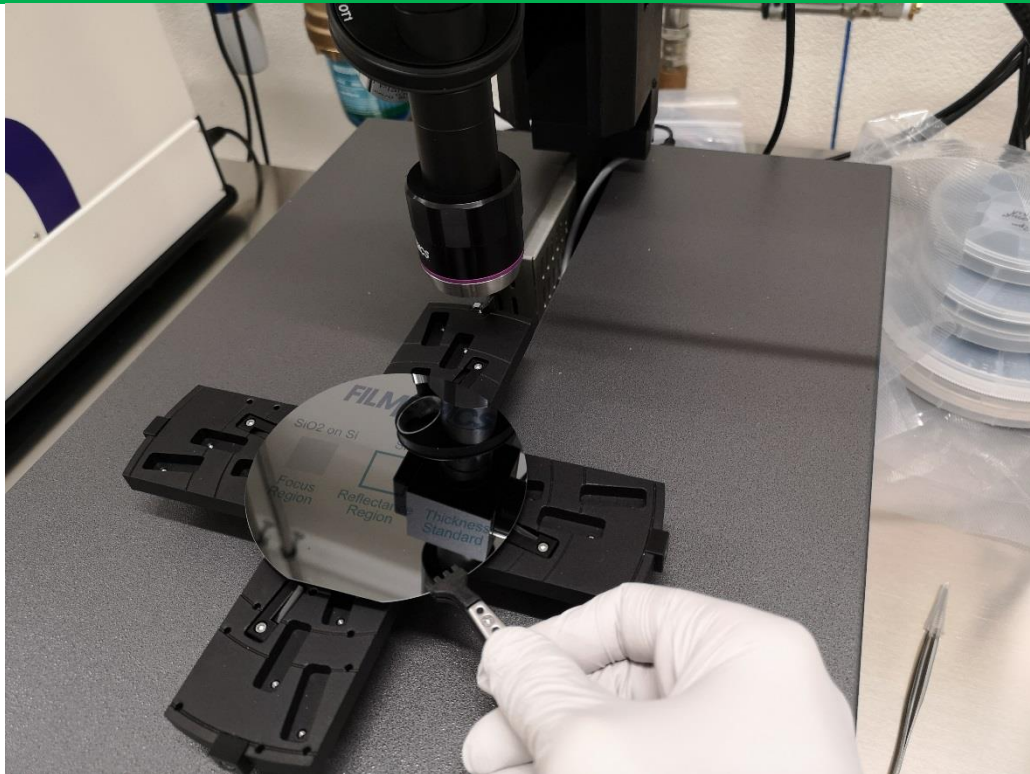
Move the stage to Load position



RISK OF DAMAGING THE OPTICS:
Do not load with stage under the objective!

Sample loading: good practice

OK (stage at 0,100)



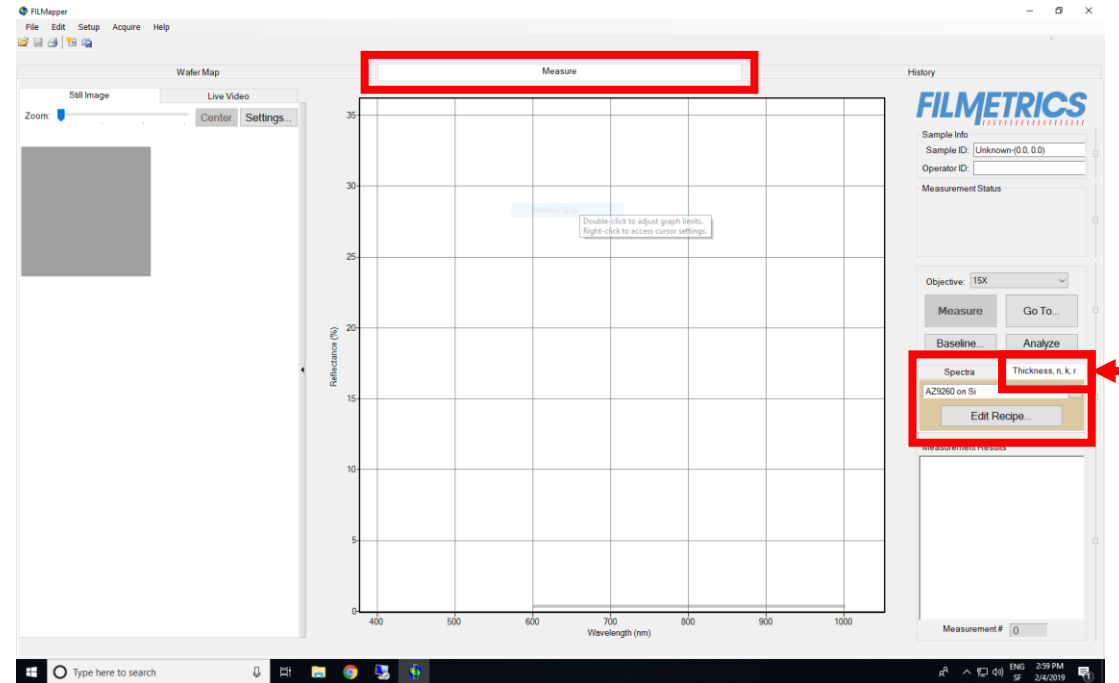
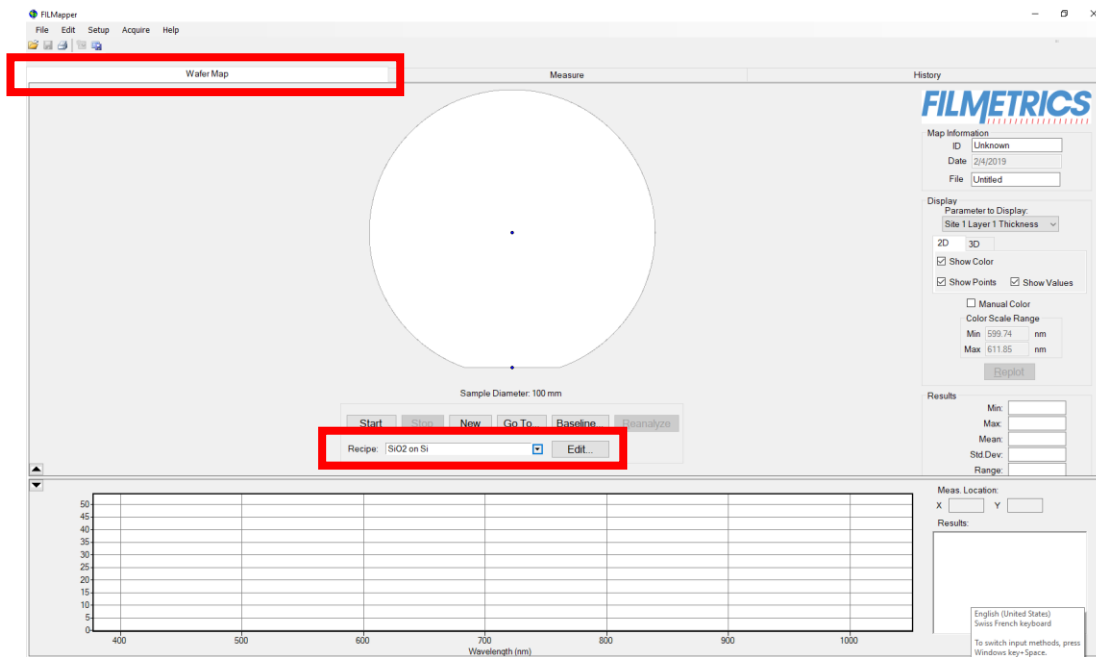
NO EXCHANGE UNDER OBJECTIVE!



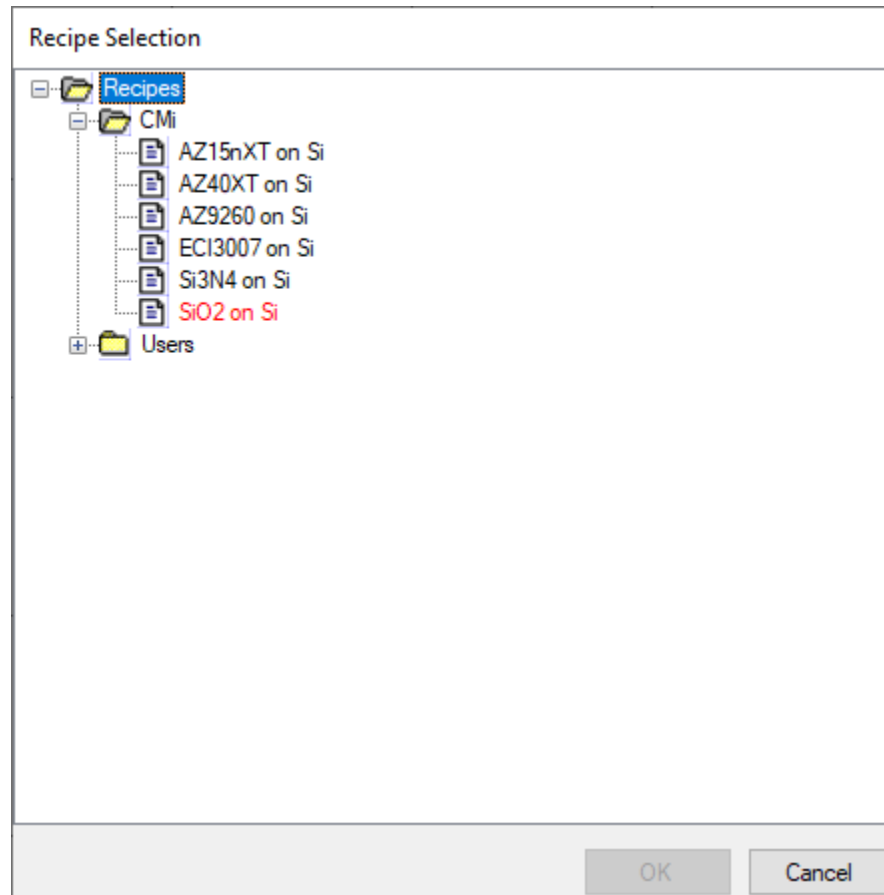
Choose a Recipe and Edit it

From **Wafer Map** tab:

From **Measurement** tab:
(Under **Thickness, n, k, r**)



Pick a Recipe



- **CMi** folder: standard recipes (DO NOT MODIFY)
- **Users** folder: custom recipes

Define the stack (**Film Stack** tab)

Recipe Name: SiO2 on Si

Author: Last Modified: 2/4/2019 2:51:38 PM

Film Stack | Analysis Options | Alarms | Wafer Map | Acquisition Settings

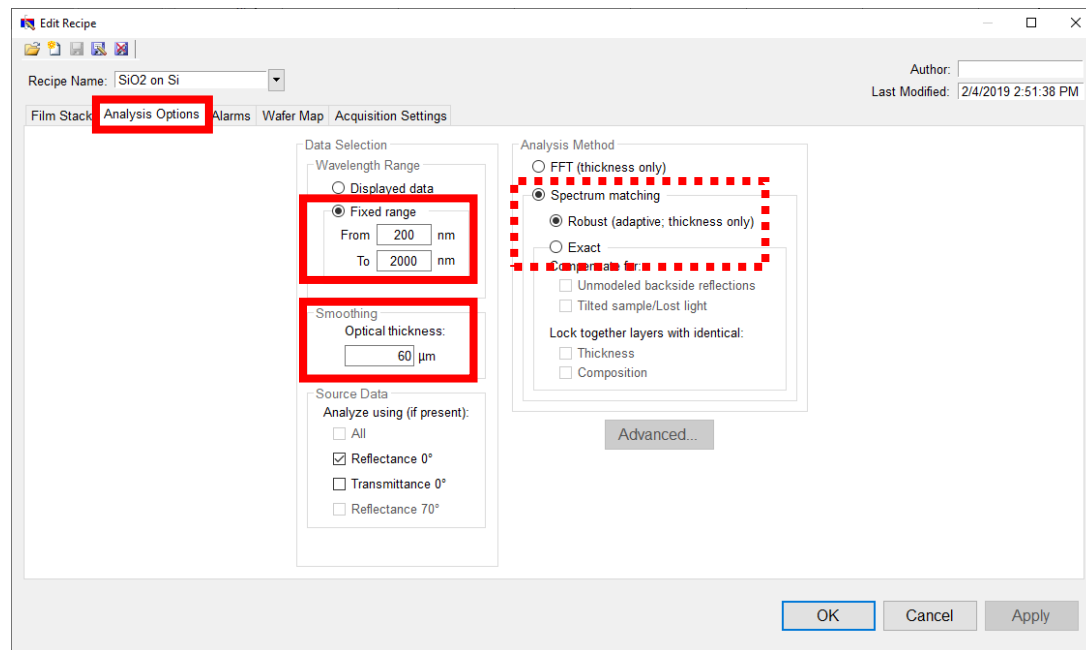
Units: Nanometers (nm)

| Layer | Composition | ±n | ±k | Meas. | Grading | Meas. | Nominal (nm) | Range (%) | Refine via | Nonuniformity (nm) | Meas. |
|-----------|-------------|----|----|--------------------------|---------|--------------------------|--------------|-----------|-------------------------------------|--------------------|----------------------------|
| Medium | Air | | | <input type="checkbox"/> | | | | | | | |
| 1 | SiO2 | | | <input type="checkbox"/> | 0 % | <input type="checkbox"/> | 1000 | ± 100 | <input checked="" type="checkbox"/> | None | 0 <input type="checkbox"/> |
| Substrate | Si | | | <input type="checkbox"/> | | | | | | | |

OK Cancel Apply

- Choose the units (μm , nm, Å)
- Define substrate/film(s)/medium
- Input expected thickness (nominal \pm range), tick to measure (enable fit)
- -> Move to **Analysis Options**

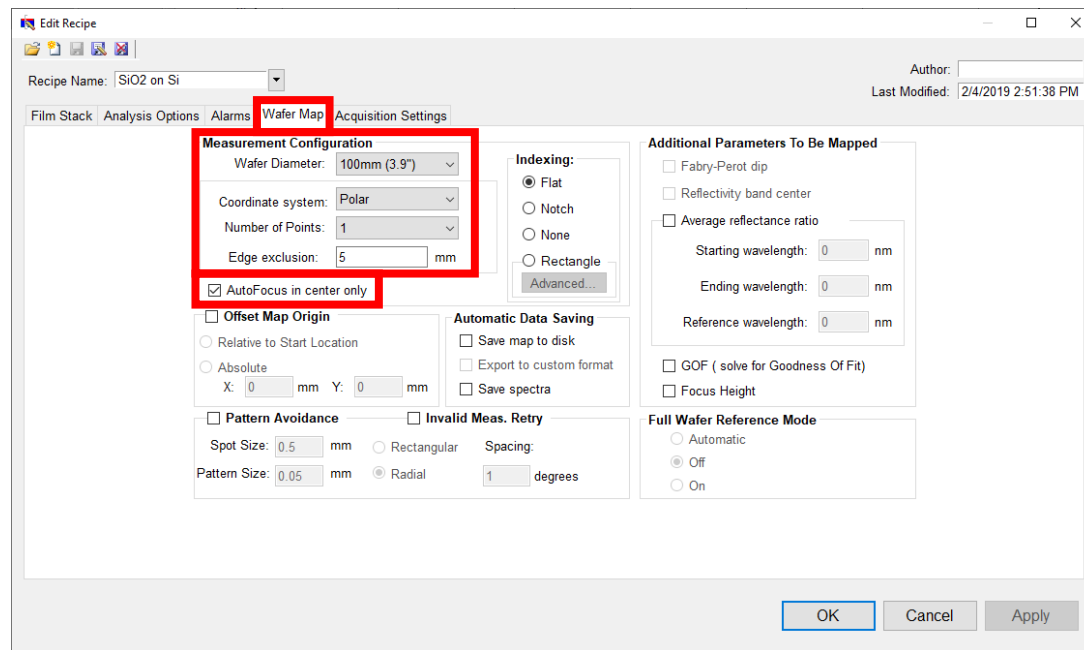
Specify Analysis Options



- Limit the Wavelength Range if appropriate
- Adjust moving-average Smoothing to denoise the spectrum (use $\geq 1000\mu\text{m}$ to disable)
- Change Method to Exact for stacks and/or thickness $< 150\text{nm}$

-> Move to Wafer Map

Choose a **Wafer Map**

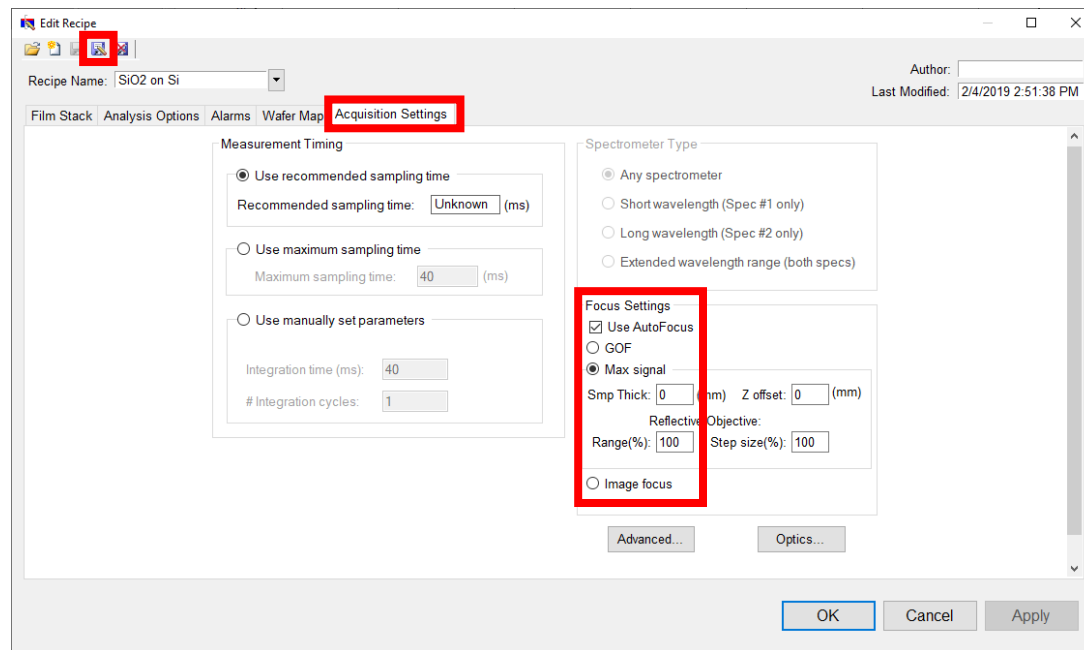


- Modify measurement configuration (sample size, number of points, exclusion, ...)
- OK to limit autofocus in center for the sake of speed

-> Move to **Acquisition Settings**

Advanced options (including Deskew) under **Wafer Map** tab: Edit -> Map Pattern...

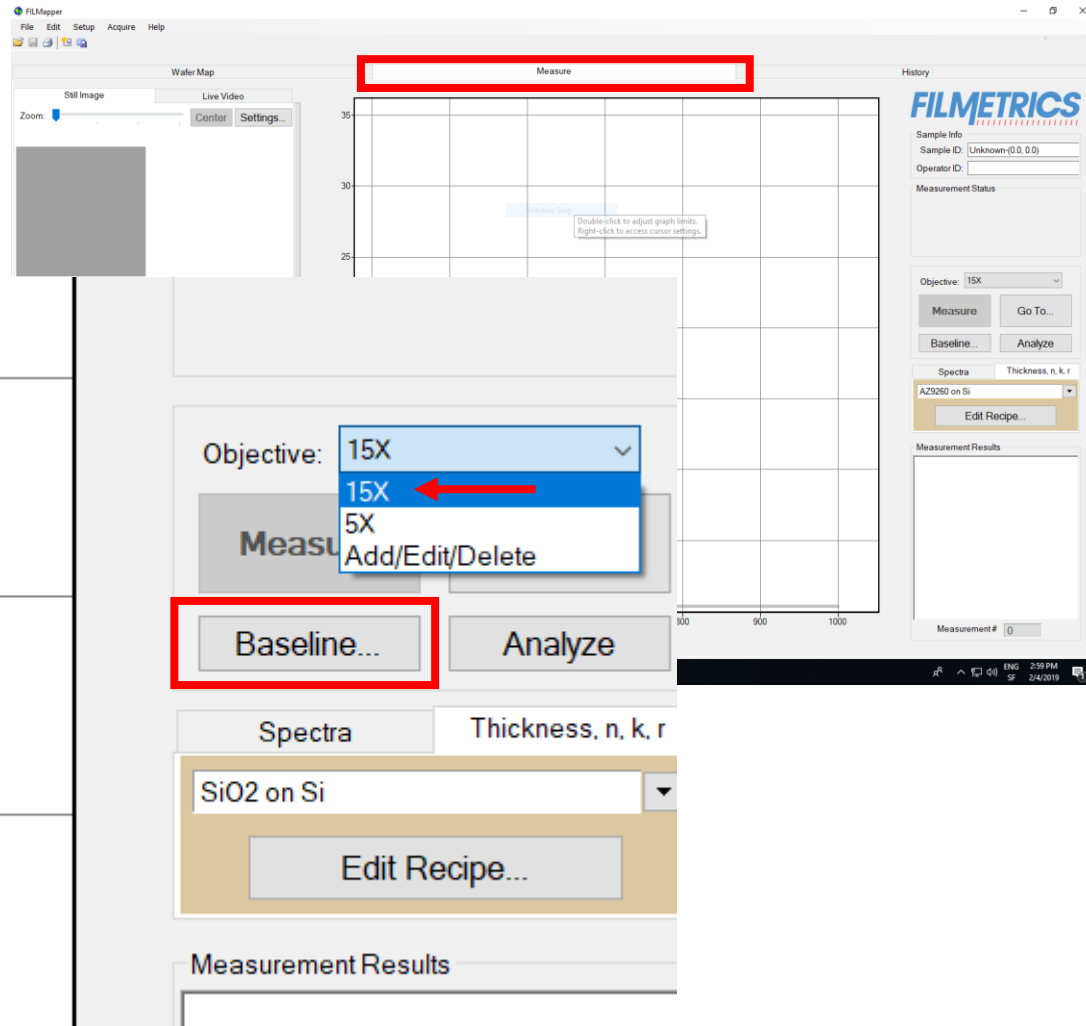
Acquisition settings



- Enable/disable **Autofocus**
- Available methods are Goodness Of Fit, Max of reflectometer signal, and Image-based focus
- Save As to create a new recipe (DO NOT OVERWRITE CMi ones)

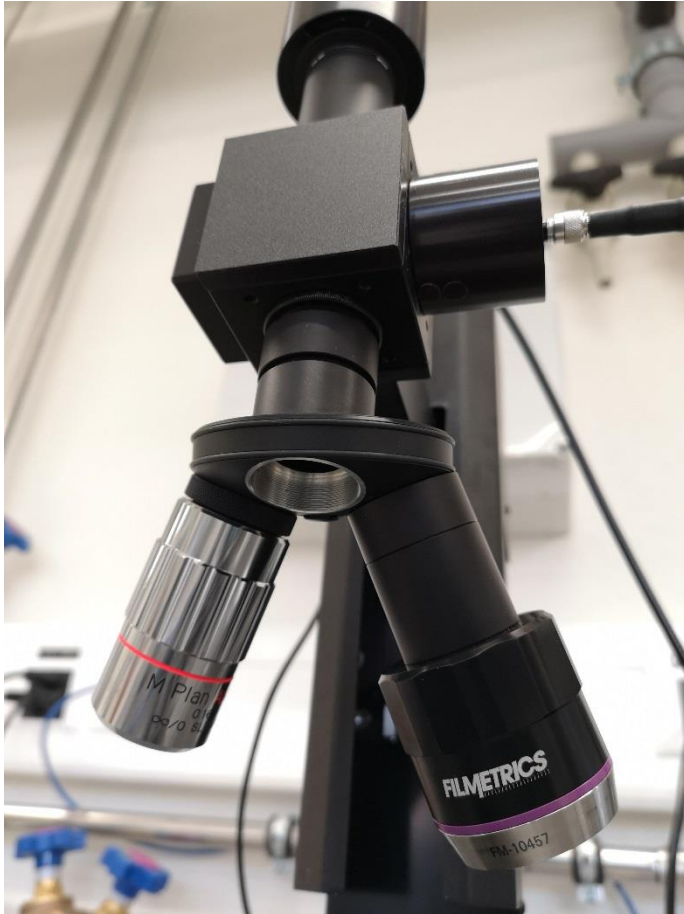
-> Acquire a **Baseline** (optional) and perform a **Measurement**

Objective and Baseline

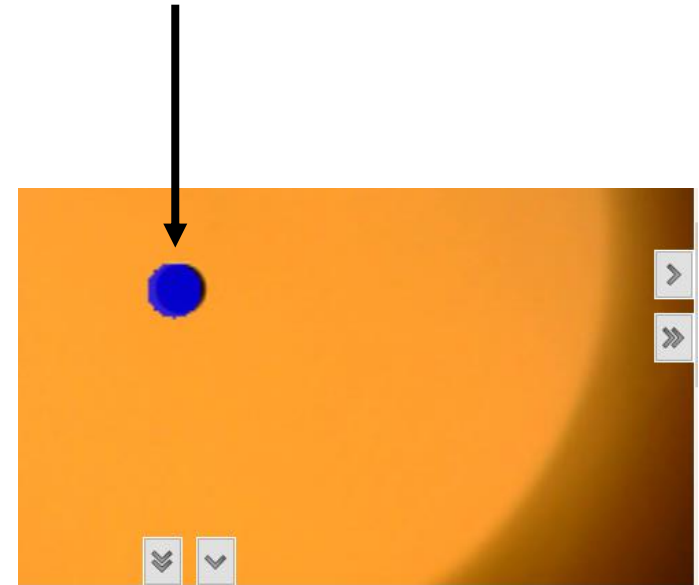


- Select the objective matching the current configuration (IMPORTANT!)
- Optional: take a Baseline measurement (lamp warm-up time ~5min)

Objectives



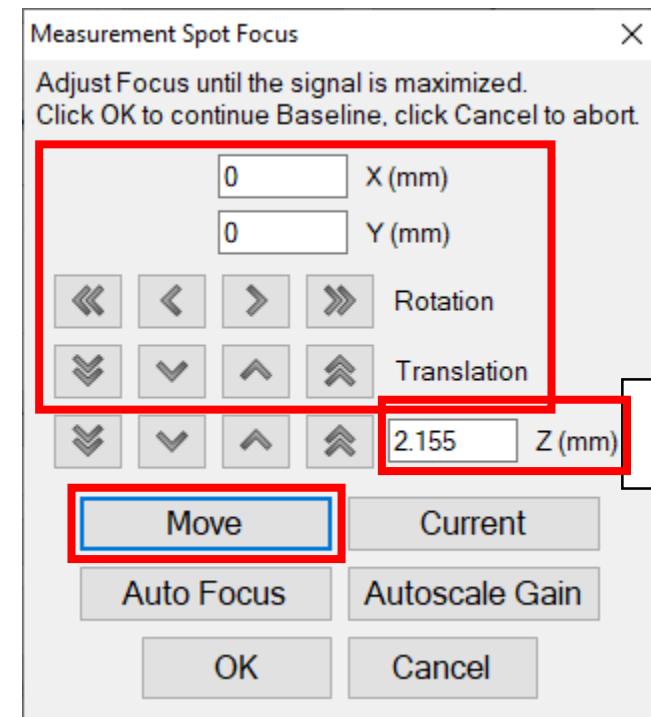
- 5x -red ring (spot size 50 μ m)
- 15x -violet ring (spot size 17 μ m)



Baseline procedure

1. Load your sample
2. Acquire sample reflectance
3. Unload sample and load reference standard (Si)
4. Acquire reference standard reflectance
5. Let the machine acquire the background (45° mirror) and align the stage
6. Unload reference standard and load your sample

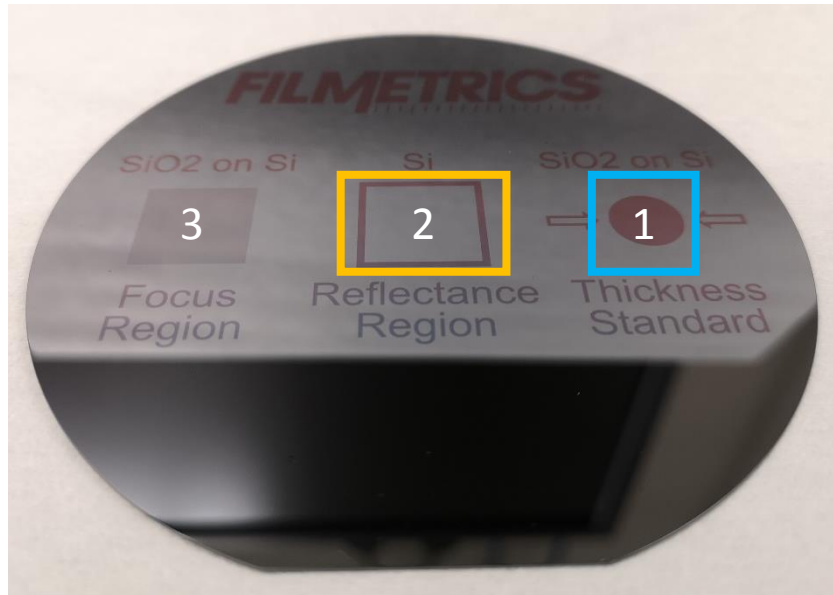
To **move** the stage (when prompted)



Height for best autofocus
on 525 μ m-thick wafers

- **Loading** position is (100,0)
- Wafer **center** is (0,0)

Baseline calibration sample for SiO₂ on Si



Filmetrics calibration sample:

1. Sample reflectance calibration region (go to 30,0)
2. Reference reflectance calibration region (go to 0,0)
3. (patterned sample region)

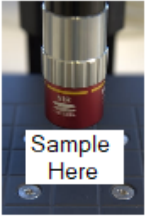
One Si wafer available for reference reflectance calibration

Baseline steps

1. Sample reflectance (your wafer)

Take Reflectance Standard Procedure

Step 1 of 2: Take Sample Reflectance



•Place sample to be measured on the stage
•Click Take Sample Reflectance

Take Sample Reflectance Override...


Status:

Recover Last Baseline... <-- Prev Next --> Cancel

2. Reflectance standard (Si wafer)

Take Reflectance Standard Procedure

Step 2 of 2: Take Reflectance Standard



•Center the Focus/Reference Wafer on stage (flat toward front)
•Click Take Reflectance Standard
(5 minute lamp warm-up recommended for best results.)*

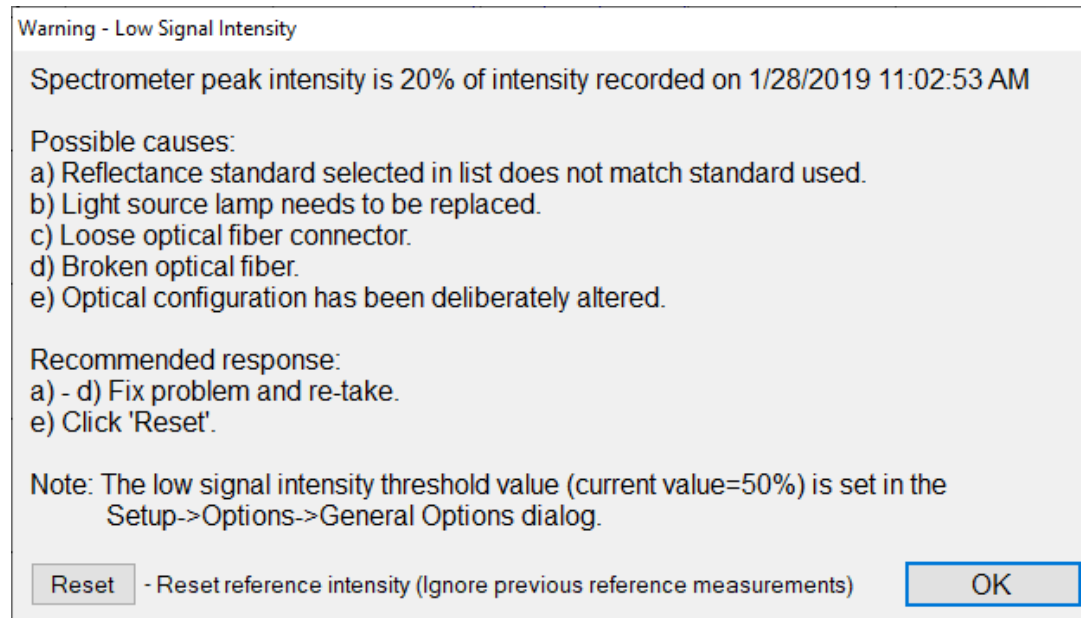
Reflectance Standard: Si

Take Reflectance Standard

Status: Not yet completed [*Warm-up Time](#)

<-- Prev Finish Cancel

Baseline warning



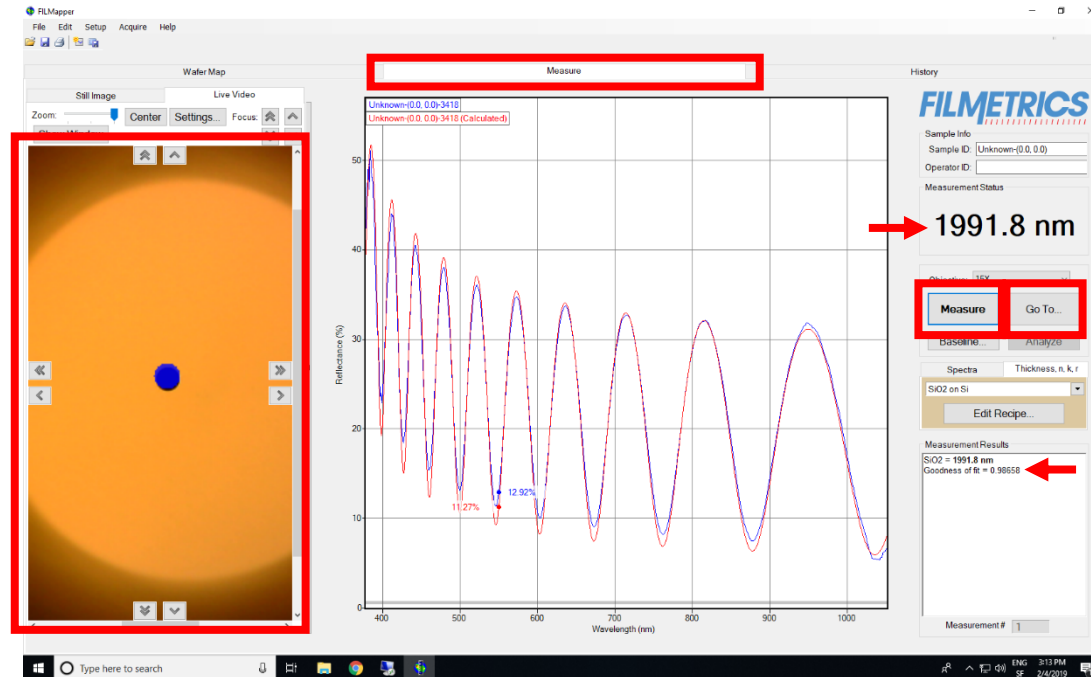
Software issues a warning in case of important **intensity difference** after new baseline

This can be due to

- Lamp state (off or burnt, not warmed-up)
- Objective used for last baseline

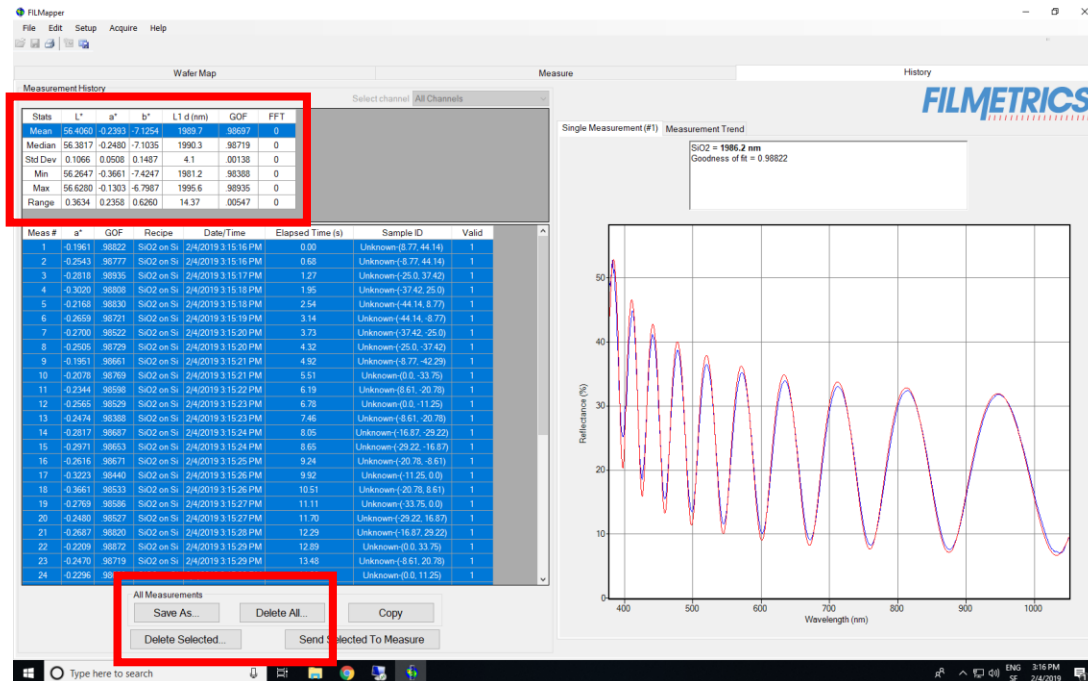
Acknowledge if it makes sense!

Point measurements



- **Navigate** to the point of interest by means of
 - camera and **r/theta controls** (arrows), or
 - **Go To...** button (wafer center: 0,0)
- **Click Measure**
Check goodness of fit (GOF)

Measurement summary (History tab)



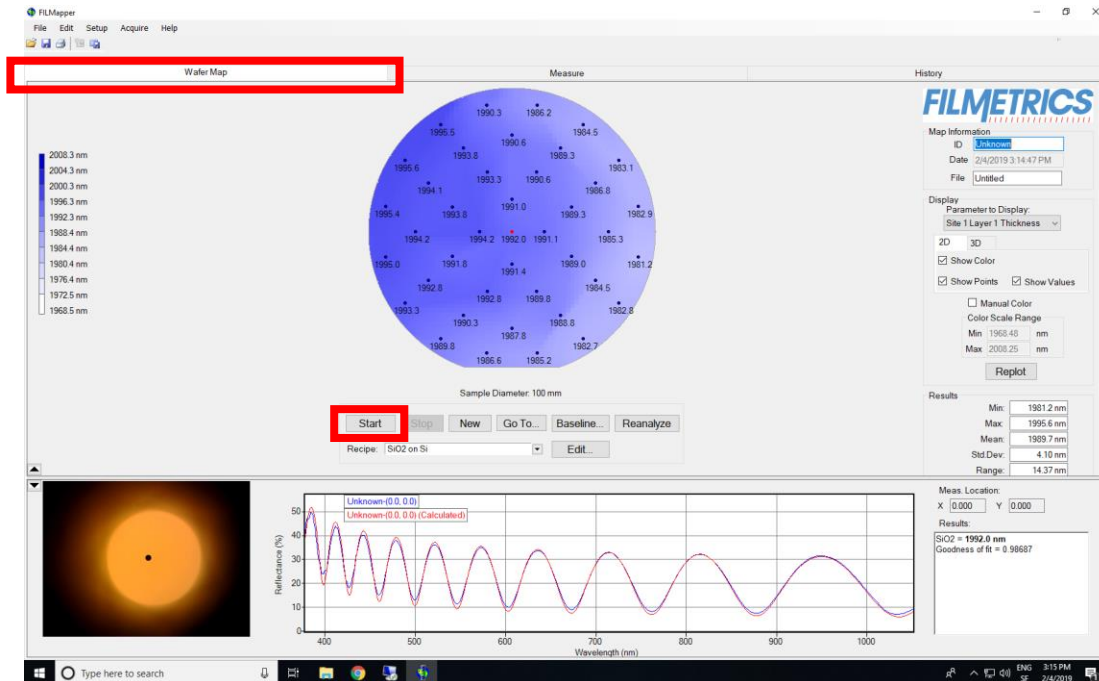
- Basic statistics available in realtime *on all stored data* => Purge history
- Export to text/spreadsheet

Wafer Mapping

Click on **Start**

Interacting with the map:

- Left click: go to point
- Right click: mark as invalid/interpolate from neighbours



Turn lamp off when done!



Tool specifications

| | |
|-------------------------|--|
| Thickness Range | ~20nm -- ~40um |
| Accuracy | 2nm or 0.2% |
| Precision | 0.2nm |
| Stability | 0.05nm |
| Wavelength range | 380-1050nm |
| Spot size | 250um aperture: 50um@5x, 17um@15x (on request) 500um aperture: 100um@5x, 33um@15x |
| Typical speed | 5 points: 5'' 25 points: 25'' 56 points: 29'' |